

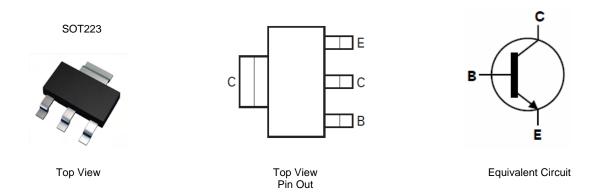
75V NPN SILICON PLANAR HIGH VOLTAGE TRANSISTOR IN SOT-223

Features and Benefits

- BV_{CEO} > 75V
- Maximum continuous current I_C= 4.5A
- 10A pulse current
- High gain holds up h_{FE} > 300 @ I_C=1A
- Very low equivalent on-resistance; $R_{CE(sat)} = 78m\Omega$ at 4.5A
- "Green" component, Lead Free Finish / RoHS compliant (Note 1)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: SOT223
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish
- Weight: 0.112 grams (approximate)



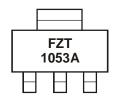
Ordering Information (Note 1)

Part Number	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
FZT1053ATA	FZT1053A	7	12	1,000

Notes: 1.

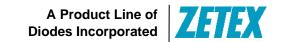
1. Diodes, Inc. defines "Green" products as those which are RoHS compliant and contain no halogens or antimony compounds. All applicable RoHS exemptions applied. Further information about Diodes Inc.'s "Green" Policy can be found on our website at http://www.diodes.com

Marking Information



FZT1053A = Product Type Marking Code





Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	150	V
Collector-Emitter Voltage	V _{CEO}	75	V
Emitter-Base Voltage	V _{EBO}	7.5	V
Continuous Collector Current	Ic	4.5	Α
Base Current	I _B	500	mA
Peak Pulse Current (Note 2)	I _{CM}	10	Α

Thermal Characteristics @TA = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector Power Dissipation (Note 2)	P _D	2.5	W
Thermal Resistance, Junction to Ambient (Note 2)	$R_{ heta JA}$	50	°C/W
Thermal Resistance, Junction to Leads (Note 3)	$R_{ heta JL}$	10.88	°C/W
Operating and Storage Temperature Range	T_{J} , T_{STG}	-55 to +150	°C

Electrical Characteristics @T_A = 25°C unless otherwise specified

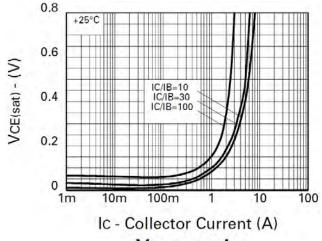
Characteristic	Symbol	Min	Тур.	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	150	250	-	V	$I_{C} = 100 \mu A$
Collector-Emitter Breakdown Voltage	BV _{CES}	150	250	-	V	$I_C = 100 \mu A$
Collector-Emitter Breakdown Voltage (Note 4)	BV _{CEO}	75	100	-	V	$I_C = 10mA$
Collector-Emitter Breakdown Voltage	BV _{CEV}	150	250	-	V	$I_C = 100 \mu A, V_{EB} = 1 V$
Emitter-Base Breakdown Voltage	BV _{EBO}	7.5	8.8	-	V	I _E = 100μA
Collector Cutoff Current	I _{CBO}	-	0.9	10	nA	V _{CB} = 120V
Collector Cutoff Current	I _{CES}	-	1.5	10	nA	V _{CES} = 120V
Emitter Cutoff Current	I _{EBO}	-	0.3	10	nA	V _{EB} = 4V
		270	440	-		$I_C = 10mA, V_{CE} = 2V$
		300	450	1200	-	$I_C = 0.5A$, $V_{CE} = 2V$
DC current transfer Static ratio (Note 4)	h _{FE}	300	450	-		$I_C = 1A$, $V_{CE} = 2V$
		40	60	-		I _C = 4.5A, V _{CE} = 2V
		-	20	-		I _C = 10A, V _{CE} = 2V
	V _{CE} (sat)	-	21	30	mV	$I_C = 0.2A$, $I_B = 20mA$
		-	55	75		$I_C = 0.5A$, $I_B = 20mA$
Collector-Emitter Saturation Voltage (Note 4)		-	150	200		$I_C = 1A, I_B = 10mA$
		-	160	210		$I_C = 2A$, $I_B = 100mA$
		-	350	440		$I_C = 4.5A, I_B = 200mA$
Base-Emitter Saturation Voltage (Note 4)	$V_{BE(sat)}$	-	900	1000	mV	$I_C = 3A$, $I_B = 100mA$
Base-Emitter Turn-on Voltage (Note 4)	V _{BE(on)}	-	825	950	mV	$I_C = 3A$, $V_{CE} = 2V$
Transitional Frequency (Note 4)	f _T	-	140	-	MHz	$I_C = 50 \text{mA}, V_{CE} = 10 \text{V},$ f = 100MHz
Output capacitance	C _{obo}	-	21	30	pF	V _{CB} = 10V, f = 1MHz,
Switching Time	t _{on}	-	162	-	ns	$V_{CC} = 50V, I_C = 2A,$
Switching Time	t _{off}	-	900	-	ns	$I_{B1} = I_{B2} = \pm 20 \text{mA}$

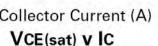
Notes:

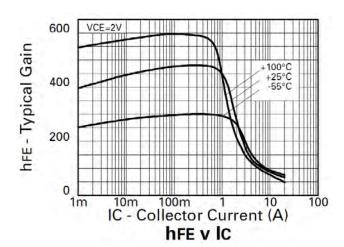
- 2. For the device mounted on 50mm x 50mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.
- 3. Thermal resistance from junction to solder-point (at the end of the drain lead)
- 4. Measured under pulsed conditions. Pulse width = 300μs. Duty cycle ≤2%.

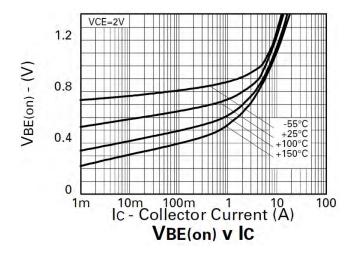


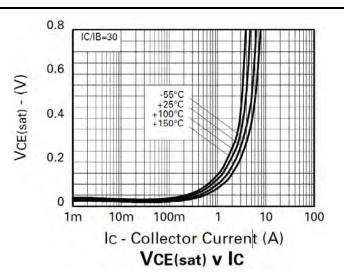
Electrical Characteristics

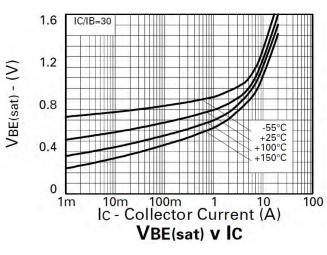


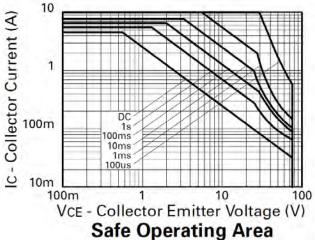






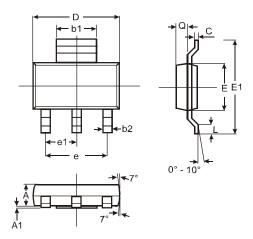






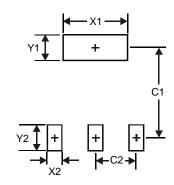


Package Outline Dimensions



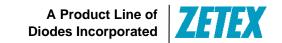
SOT223				
Dim	Min	Max	Тур	
Α	1.55	1.65	1.60	
A 1	0.010	0.15	0.05	
b1	2.90	3.10	3.00	
b2	0.60	0.80	0.70	
С	0.20	0.30	0.25	
D	6.45	6.55	6.50	
Е	3.45	3.55	3.50	
E1	6.90	7.10	7.00	
е	_	_	4.60	
e1	_		2.30	
L	0.85	1.05	0.95	
Ø	0.84	0.94	0.89	
All Dimensions in mm				

Suggested Pad Layout



Dimensions	Value (in mm)
X1	3.3
X2	1.2
Y1	1.6
Y2	1.6
C1	6.4
00	0.0





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Офис по работе с юридическими лицами:

105318, г. Москва, ул. Щербаковская д. 3, офис 1107, 1118, ДЦ «Щербаковский»

Телефон: +7 495 668-12-70 (многоканальный)

Факс: +7 495 668-12-70 (доб.304)

E-mail: info@moschip.ru

Skype отдела продаж:

moschip.ru moschip.ru_6 moschip.ru 4 moschip.ru 9